



YJD05C90HJ

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**N-Channel Enhancement Mode Field Effect Transisreltr**



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### Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D$	900	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=900V, V_{GS}=0V$	-	-	1	
		$V_{DS}=900V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	$\pm 100$	nA



## Typical Electrical and Thermal Characteristics Diagrams

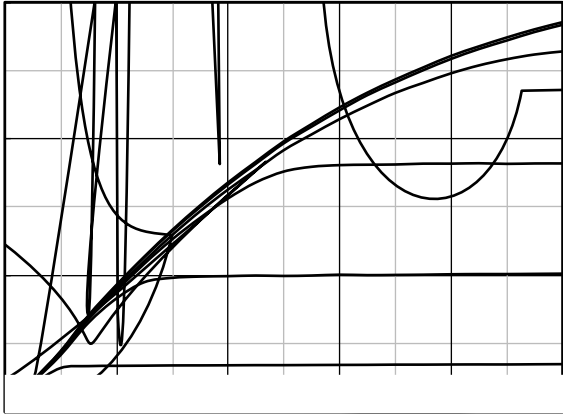


Figure 1. Output Characteristics

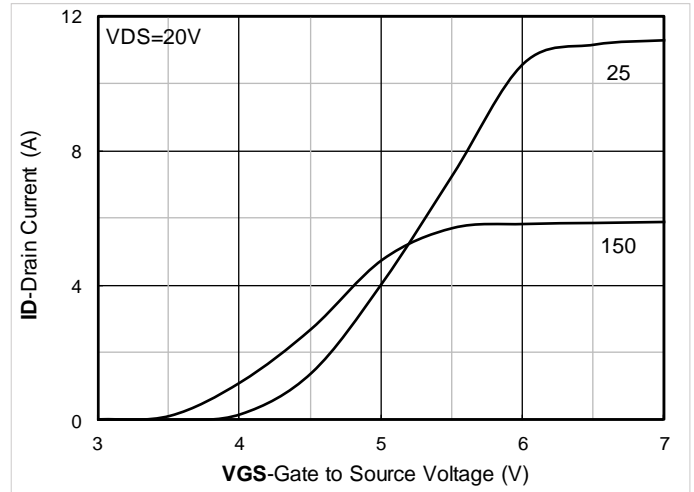


Figure 2. Transfer Characteristics

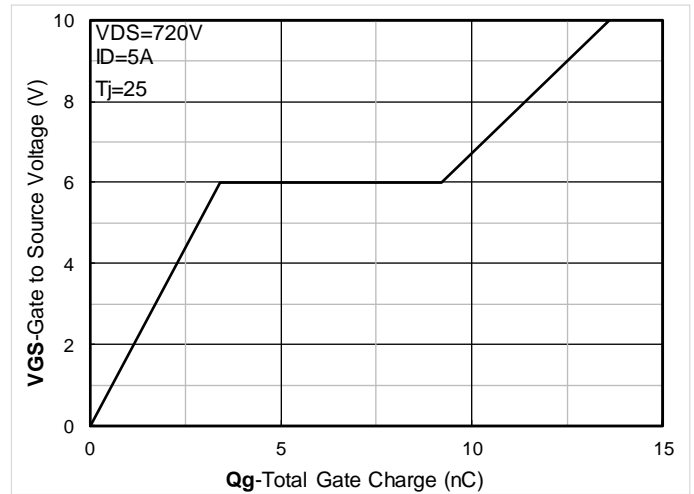


Figure 3. Capacitance Characteristics

Figure 4. Gate Charge

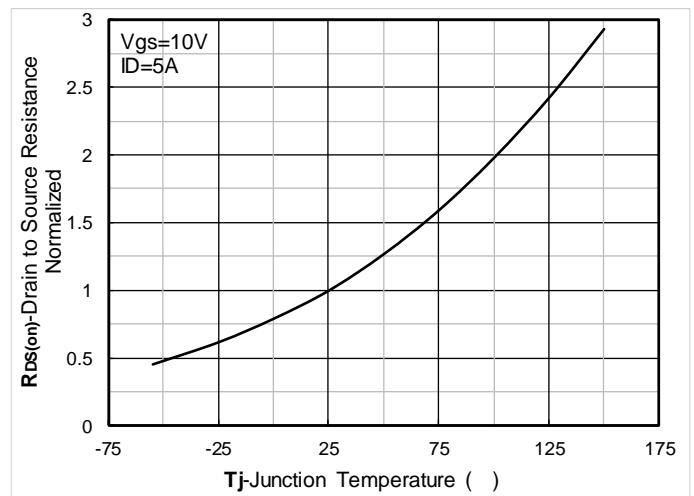


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance

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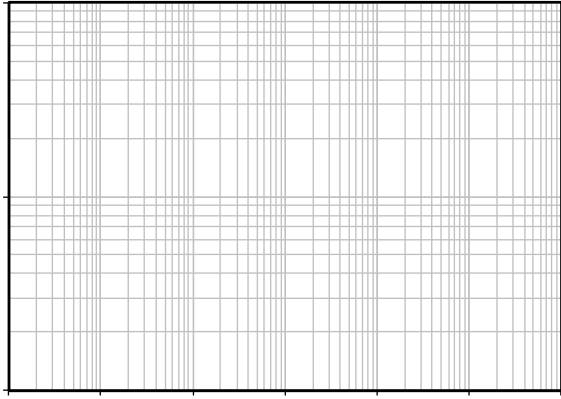


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

## Test Circuits & Waveforms

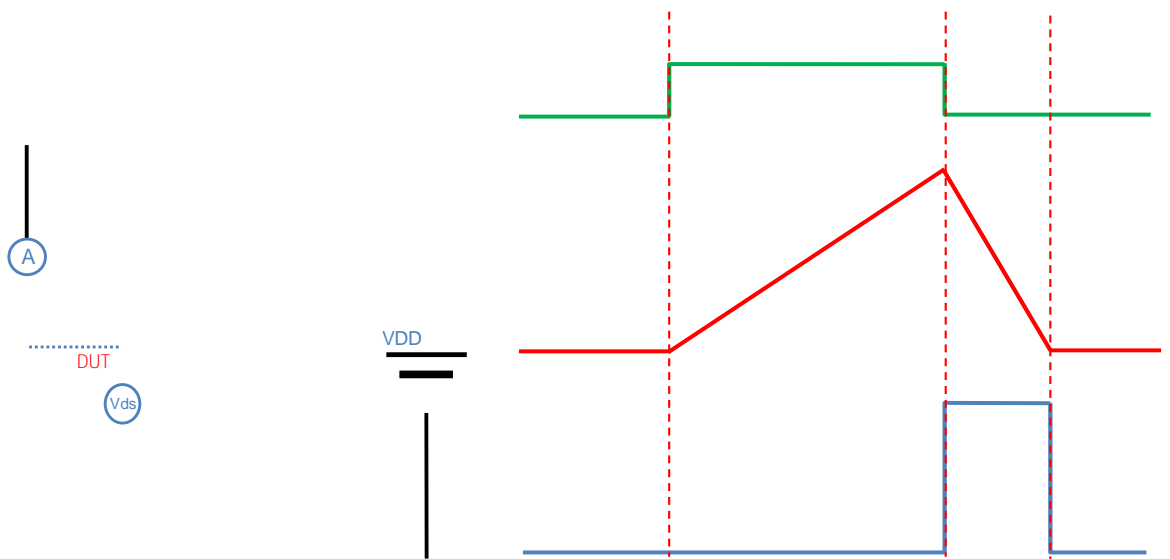


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

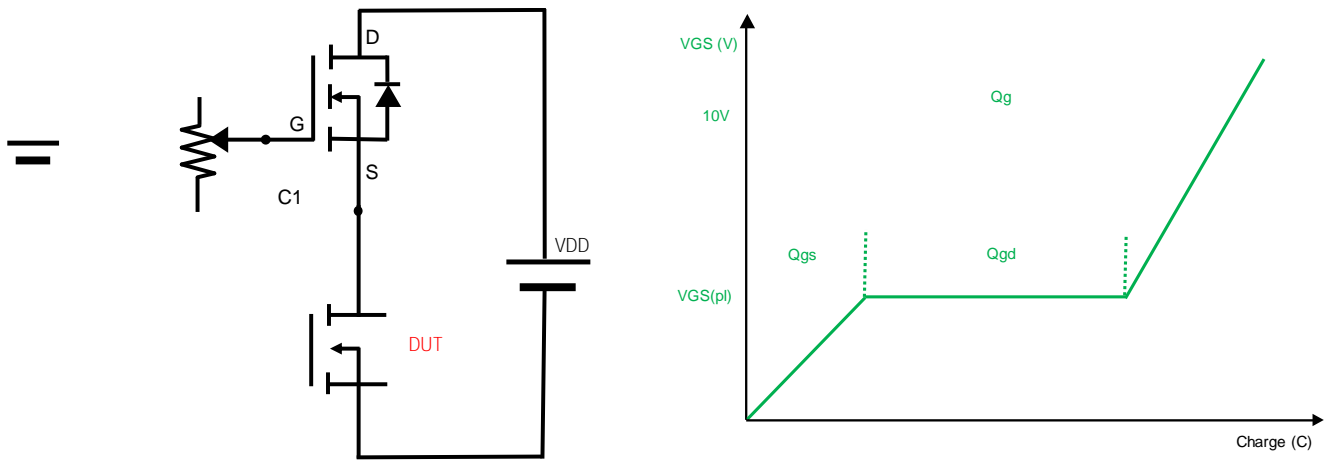


Figure B. Gate Charge Test Circuit & Waveform

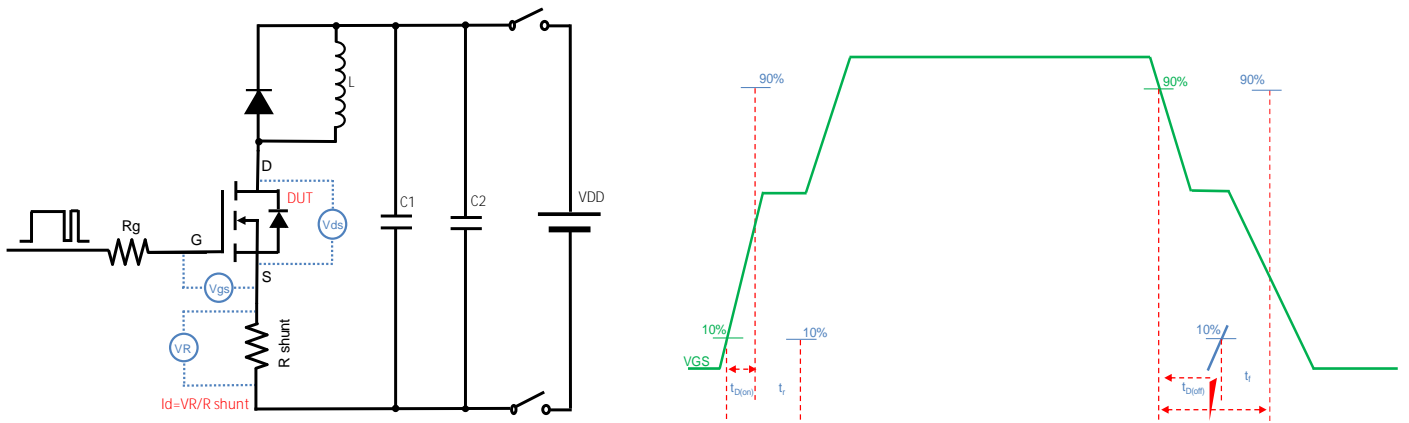


Figure C. Resistive Switching Test Circuit & Waveform



Figure D. Diode Recovery Test Circuit & Waveform





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